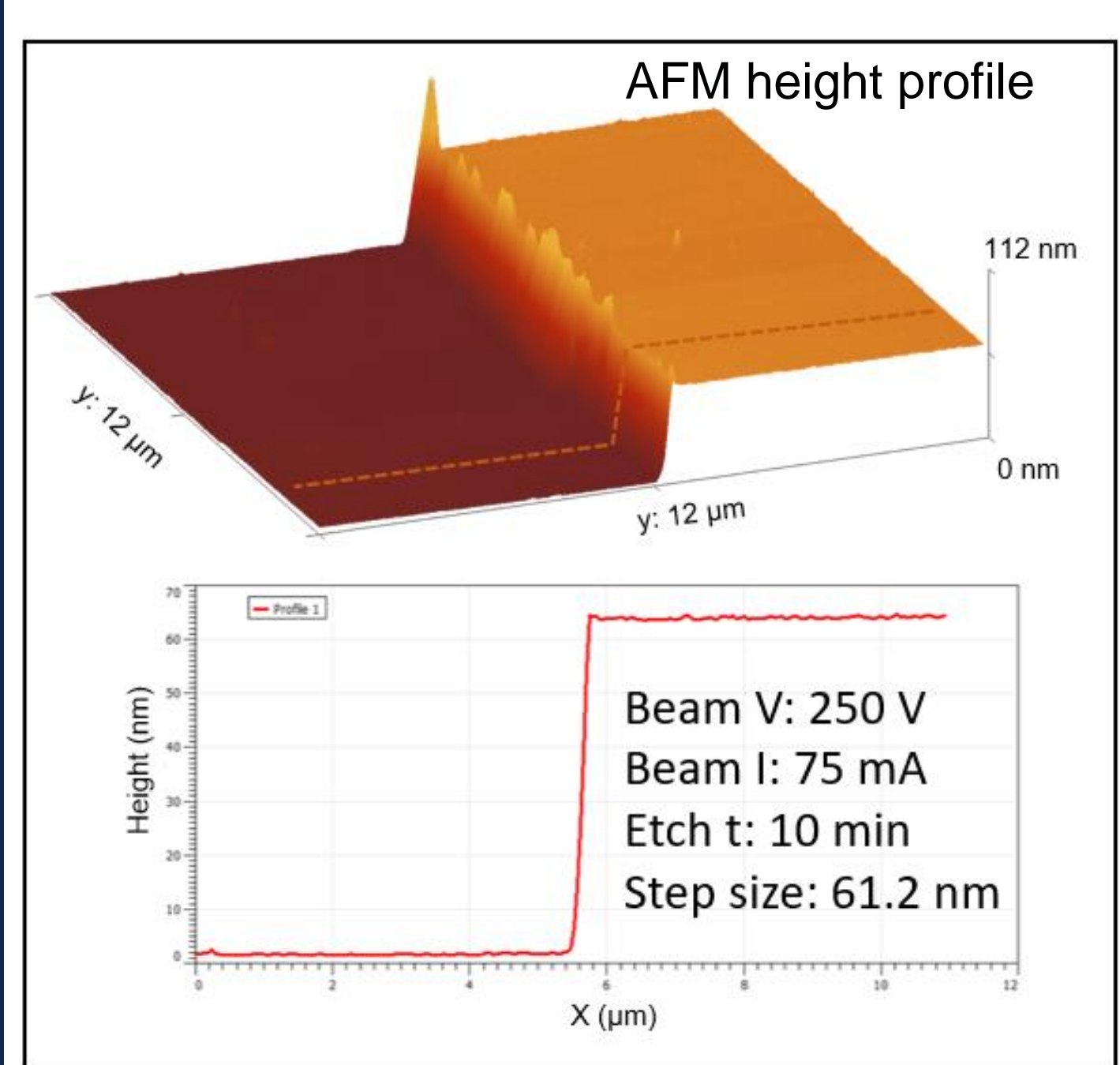


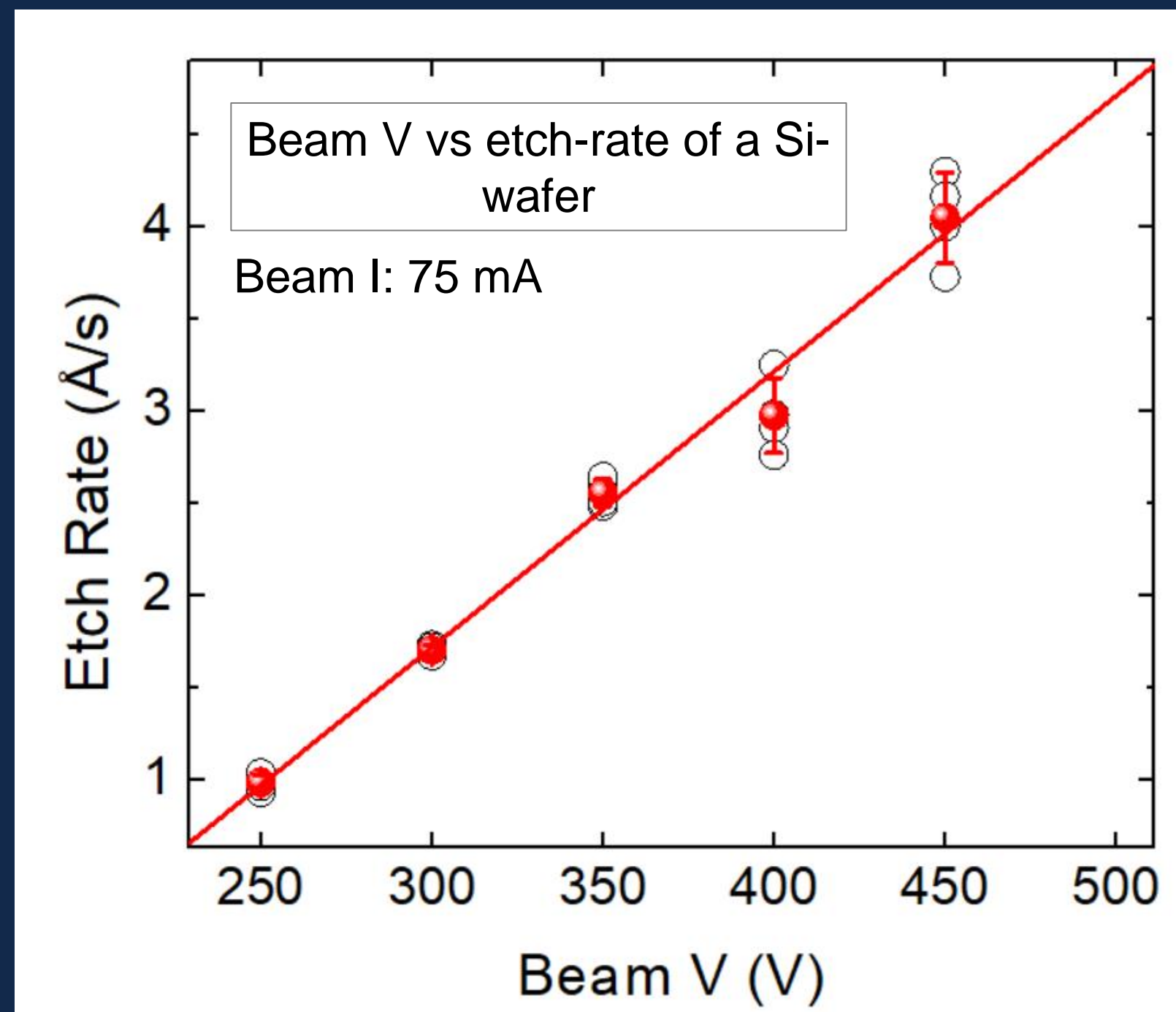
- Integrated ion milling and thermal evaporation capability
- Dedicated to the deposition of:

- ❖ Cu
- ❖ Pb
- ❖ In
- ❖ Au
- ❖ Ag
- ❖ Fe
- ❖ MoO<sub>3</sub>
- ❖ Al
- ❖ Sn
- ❖ Sb
- ❖ Cr
- ❖ Ni
- ❖ Ti

and more.

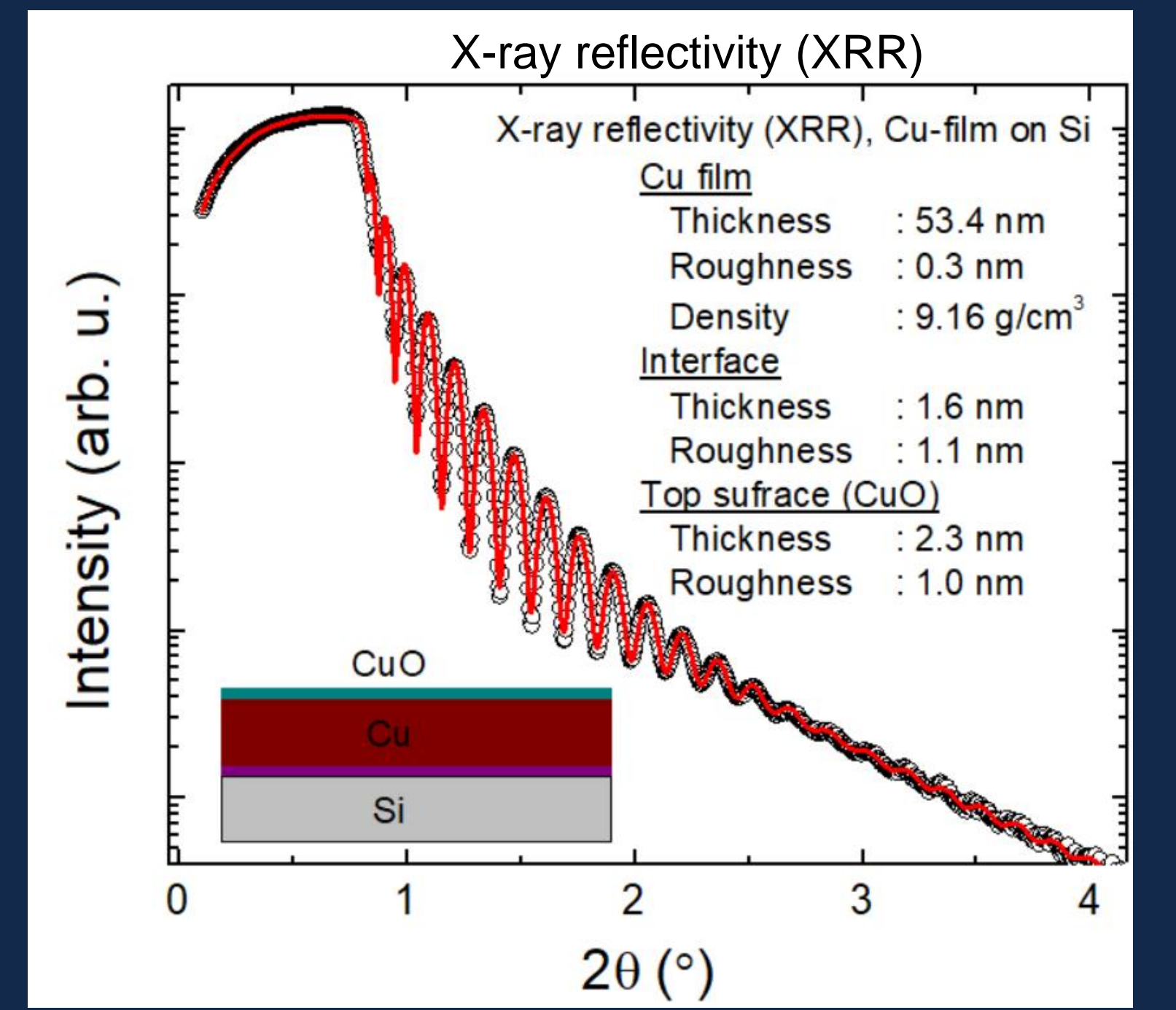
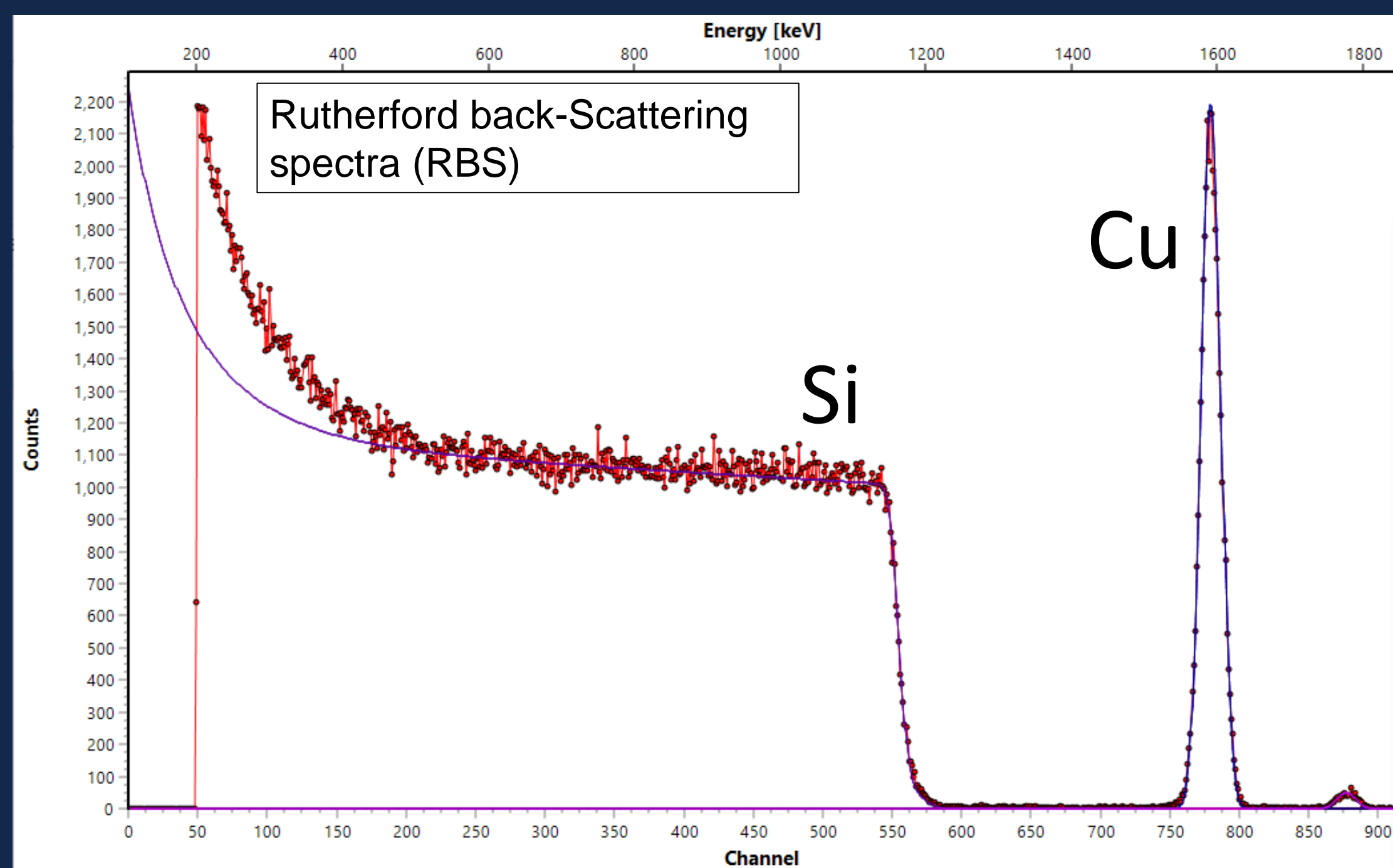
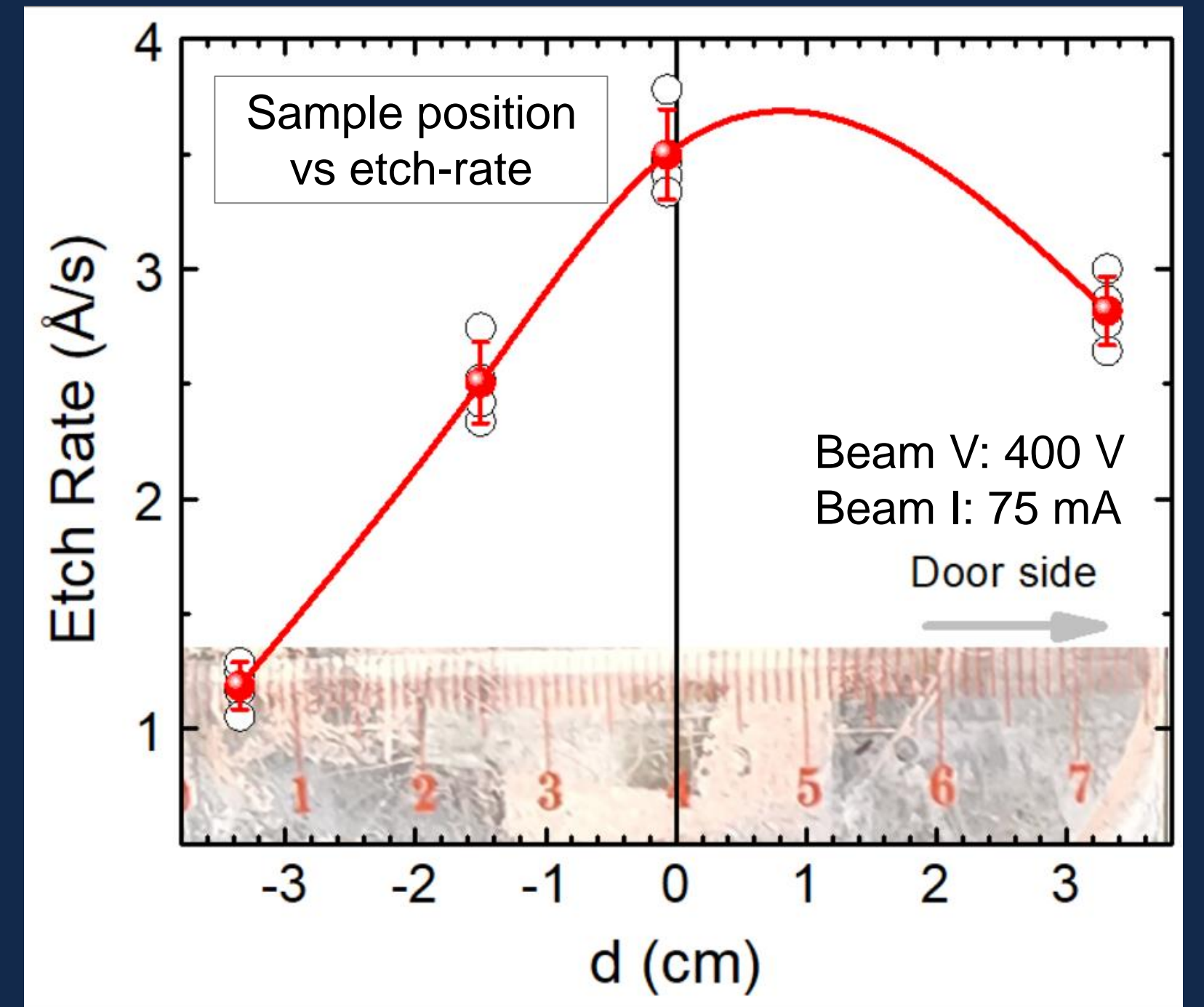


- A sharp step on the silicon surface etched using Commonwealth ion mill (up)

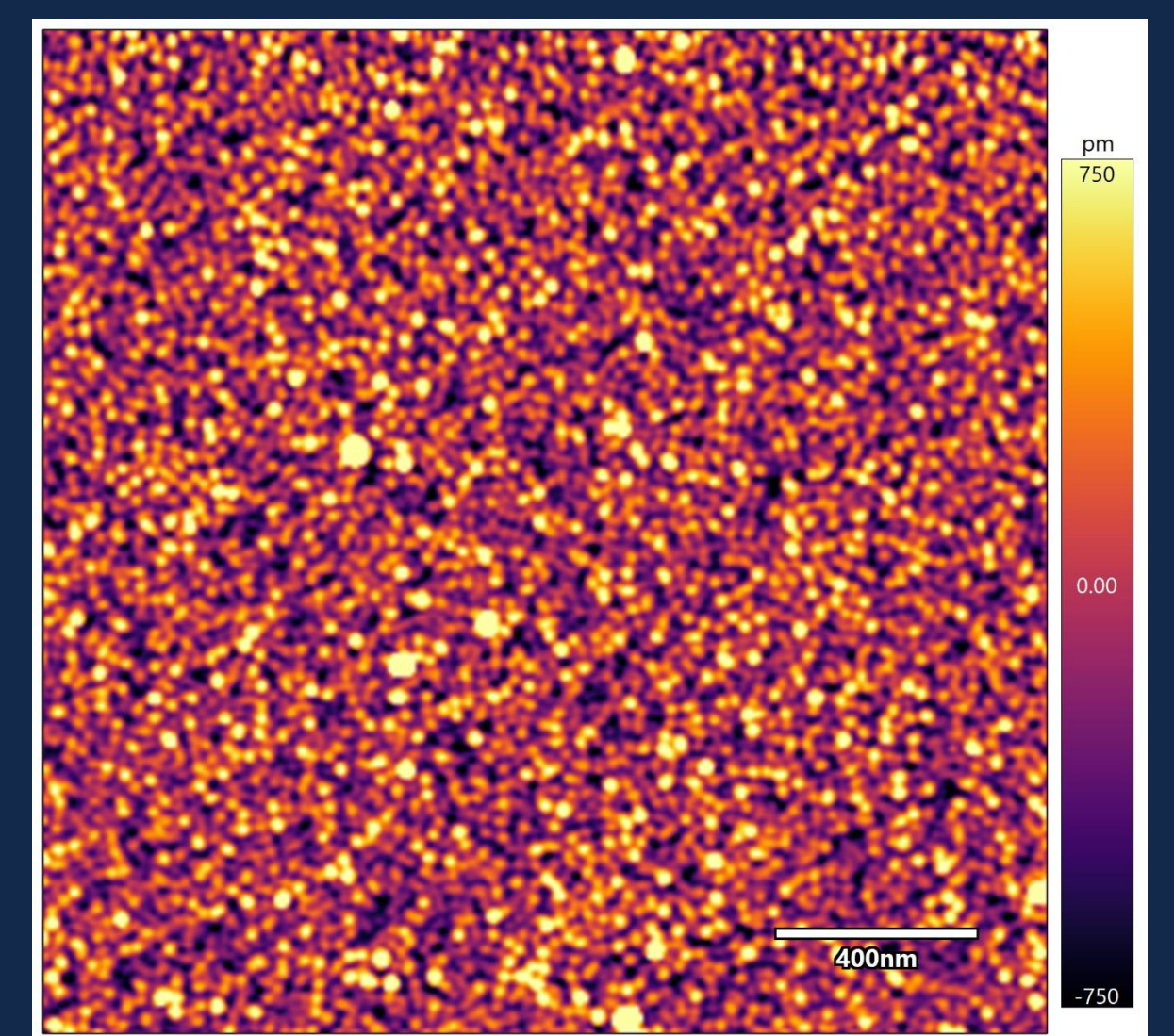


- Highly focused ion beam near the center of the sample stage

- Beam voltage (V) and/or beam current (I) can be varied to obtain the desired etch-rate



- Rutherford back-scattering (RBS) spectrum measured from a 15 nm Cu-film deposited on a Si wafer using the Commonwealth Thermal Evaporator (up)
- X-ray reflectivity (XRR) measured from a 53.4 nm Cu-film grown on Si wafer with a GenX simulation (top right)
- Atomic force microscopy (AFM) surface scan of an atomically flat Cu-film grown on Si-wafer (RMS roughness: 380 pm) (bottom right)



AFM surface scan